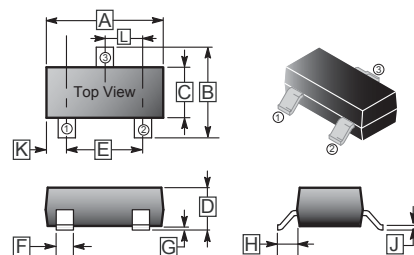


RoHS Compliant Product  
A suffix of "-C" specifies halogen & lead-free

SC-59

## DESCRIPTION

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $R_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.



## FEATURES

- Low  $R_{DS(on)}$  provides higher efficiency and extends battery life.
- Low thermal impedance copper leadframe SC-59 saves board space.
- Fast switching speed.
- High performance trench technology.

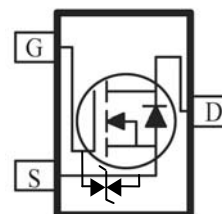
REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	0.10	REF.
B	2.25	3.00	H	0.40	REF.
C	1.30	1.70	J	0.10	0.20
D	1.00	1.40	K	0.45	0.55
E	1.70	2.30	L	0.85	1.15
F	0.35	0.50			

## PACKAGE INFORMATION

Package	MPQ	LeaderSize
SC-59	3K	7' inch



ESD  
Protection  
Diode  
2KV



## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current <sup>1</sup>	$I_D$	$T_A=25^\circ\text{C}$	6.3
		$T_A=70^\circ\text{C}$	5.2
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	20	A
Continuous Source Current (Diode Conduction) <sup>1</sup>	$I_S$	1.6	A
Power Dissipation <sup>1</sup>	$P_D$	$T_A=25^\circ\text{C}$	1.3
		$T_A=70^\circ\text{C}$	0.9
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 ~ 150	$^\circ\text{C}$
<b>Thermal Resistance Data</b>			
Maximum Junction to Ambient <sup>1</sup>	$t \leq 5$ sec	$R_{\theta JA}$	100
	Steady-State		166

Notes:

1. Surface Mounted on 1" x 1" FR4 Board.
2. Pulse width limited by maximum junction temperature.

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
<b>Static</b>						
Gate-Threshold Voltage	$V_{GS(th)}$	0.4	-	-	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Gate-Body Leakage	$I_{GSS}$	-	-	$\pm 100$	nA	$V_{DS} = 0\text{V}, V_{GS} = \pm 8\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$
		-	-	10		$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}, T_J=55^\circ\text{C}$
On-State Drain Current <sup>1</sup>	$I_{D(ON)}$	10	-	-	A	$V_{DS} = 5\text{V}, V_{GS} = 4.5\text{V}$
Drain-Source On-Resistance <sup>1</sup>	$R_{DS(ON)}$	-	-	22	m $\Omega$	$V_{GS} = 4.5\text{V}, I_D = 6.5\text{A}$
		-	-	26		$V_{GS} = 2.5\text{V}, I_D = 5.8\text{A}$
Forward Transconductance <sup>1</sup>	$g_{FS}$	-	11.3	-	S	$V_{DS} = 10\text{V}, I_D = 6.5\text{A}$
Diode Forward Voltage	$V_{SD}$	-	0.75	-	V	$I_S = 1.6\text{A}, V_{GS} = 0\text{V}$
<b>Dynamic <sup>2</sup></b>						
Total Gate Charge	$Q_g$	-	13.4	-	nC	$I_D = 6.5\text{A}$ $V_{DS} = 10\text{V}$ $V_{GS} = 4.5\text{V}$
Gate-Source Charge	$Q_{gs}$	-	0.9	-		
Gate-Drain Charge	$Q_{gd}$	-	2.0	-		
Turn-On Delay Time	$T_{d(ON)}$	-	8	-	nS	$I_D = 1\text{A}, V_{DD} = 10\text{V}$ $V_{GEN} = 4.5\text{V}$ $R_L = 15\Omega$
Rise Time	$T_r$	-	24	-		
Turn-Off Delay Time	$T_{d(OFF)}$	-	35	-		
Fall Time	$T_f$	-	10	-		

Notes:

1. Pulse test :  $PW \leq 300 \mu\text{s}$  duty cycle  $\leq 2\%$ .
2. Guaranteed by design, not subject to production testing.